

# ARFTG 71st Conference - Technical Sessions

## Session 1

**50 years of VNAs**  
**08:00–09:40**

*Chair:* Nick Ridler

**Network Analyzers – 50 Years On**  
(Keynote – invited)  
D K Rytting  
*Rytting Consulting, Santa Rosa, CA, USA*

**Network Analyzer Calibrations – Yesterday, Today and Tomorrow**  
K Wong  
*Agilent Technologies, Santa Rosa, CA, USA*

**Using Uncertain Complex Numbers with VNA Measurements**  
B D Hall  
*Measurement Standards Laboratory of New Zealand, New Zealand*

## Session 2

**VNA calibration**  
**10:20–12:00**

*Chair:* Dave Blackham

**Monte-Carlo Analysis of Measurement Uncertainties for On-Wafer Thru-Reflect-Line Calibrations**  
J Leinhos<sup>1,2</sup> and U Arz<sup>2</sup>  
<sup>1</sup>*Leibniz Universität Hannover, Germany;* <sup>2</sup>*Physikalisch-Technischen Bundesanstalt (PTB), Germany*

**A Mixed-Mode TRL Algorithm Based on Symmetrical Reflection Standards**  
W Liang<sup>1</sup> and L Quanli<sup>2</sup>  
<sup>1</sup>*Beijing University of Aeronautics and Astronautics, Beijing, China;* <sup>2</sup>*Agilent Technologies, Beijing, China*

**Accurate Broadband RLCG-Parameter Extraction with TRL Calibration**  
M Wojnowski<sup>1</sup>, M Engl<sup>1</sup>, V Issakov<sup>1</sup>, G Sommer<sup>1</sup> and R Weigel<sup>2</sup>  
<sup>1</sup>*Infineon Technologies AG, Neubiberg, Germany;* <sup>2</sup>*University of Erlangen-Nuremberg, Germany*

**Over-Determined Offset Short Calibration of a VNA**  
J P Hoffmann, P Leuchtmann and R Vahldieck  
*ETH Zurich, Zurich, Switzerland*

## Session 3

**Passive components**  
**13:30–14:45**

*Chair:* Andrea Ferrero

**A New Method for Determining the Characteristic Impedance  $Z_c$  of Transmission Lines Embedded in Symmetrical Transitions**  
J E Zúñiga-Juárez, J A Reynoso-Hernández and A Zárate-de Landa  
*CICESE, Ensenada, B C México*

**Analysis and Design of Coupled Coplanar Stripline Balun Probe for Differential Circuit Measurements**  
J S Kim<sup>1</sup>, W R Eisenstadt<sup>1</sup>, M Andrew<sup>2</sup> and P Hanaway<sup>2</sup>  
<sup>1</sup>*University of Florida, FL, USA;* <sup>2</sup>*Cascade Microtech Inc, Beaverton, OR, USA*

**Comparison of a Single Channel and a Dual Channel Microwave Attenuation Measurement System**  
T Y Wu and S W Chua  
*National Metrology Centre, Singapore*

**A Load-Pull Wafer-Mapper**  
F Vanaverbeke, K Vaesen, D Xiao, L Pauwels, W De Raedt, M Germain, S Degroote, J Das, J Derluyn and D Schreurs  
*IMEC vzw, Kapeldreef, Belgium*

**Quantitative Understanding of the Mated Interface Characteristics of Precision Coaxial Connectors at Microwave and Millimeter-Wave Frequencies**  
M Horibe, M Shida and K Komiyama  
*National Metrology Institute of Japan, Japan*

## Session 4

**Active devices**  
**15:15–16:40**

*Chair:* Ed Godshalk

**Phase Shift De-Skew of Oscilloscope Current and Voltage Sensing Probes by Means of Energy Balance**  
P Molina-Gaudó and C Bernal  
*University of Zaragoza, Zaragoza, Spain*

**Characterization of Active Harmonic Phase Standard with Improved Characteristics for Nonlinear Vector Network Analyzer Calibration**  
D Gunyan and Y-P Teoh  
*Agilent Technologies, Santa Rosa, CA, USA*

**An Extension of Existing Real-Time On-wafer Load Pull Systems to Perform Time Domain Voltage/Current Waveform Reconstruction**  
I Volokhine  
*NXP-TSMC Research Center, Eindhoven, The Netherlands*

## ARFTG Interactive Forum

**09:40–10:20 and 14:45–15:15**

*Chair:* Chris Ward

**An advanced Full Path Loop-Back Testing Technique for Embedded RF Identification (RFID) System-on-a-Chip (SoC) Applications**  
B Kim, I-C Park, D Yoo, J Koo, I Kim, B-W Choi, Y Bae and B-Y Kim  
*Samsung Electronics Co Ltd, Gyeonggi-Do, South Korea*

**Measurement Uncertainty of Direct Power Measurement Using the Pulse Sensor MA2411B**  
Y-S (B) Lee  
*Anritsu Corporation, Morgan Hill, CA, USA*

**Characterization of Carbon Nanotube Field Effect Transistors using an Active Load Pull LSNA setup**  
C Gaquière<sup>1</sup>, A Curutchet<sup>2</sup>, D Théron<sup>1</sup>, M Werquin<sup>3</sup>, D Ducatteau<sup>1</sup>, J M Bethoux<sup>1</sup>, H Happy<sup>1</sup>, G Dambrine<sup>1</sup> and V Derycke<sup>4</sup>  
<sup>1</sup>*IEMN, France;* <sup>2</sup>*IMS, France;* <sup>3</sup>*Microwave Characterization Center, France;* <sup>4</sup>*CEA – Saclay, France*

**High-Power On-Wafer Capabilities of a Time Domain Load-pull Setup**  
F De Groote<sup>1</sup>, J-P Teyssier<sup>1,2</sup>, J Verspecht<sup>1</sup> and J Faraj<sup>2</sup>  
<sup>1</sup>*Verspecht-Teyssier-DeGroote SAS, Brive, France;* <sup>2</sup>*Limoges University, Brive, France*

**Verification of Wafer-Level Calibration Accuracy at High Temperatures**  
A Rumiantsev<sup>1</sup> and R Doerner<sup>2</sup>  
<sup>1</sup>*SUSS MicroTec Test Systems GmbH, Sacka, Germany;* <sup>2</sup>*Ferdinand-Braun-Institut fuer Hoehstfrequenztechnik (FBH), Berlin, Germany*

**A Proposed VNA Calibration Requirement for Chinese Government**  
L Xinmeng and H Hui  
*National Institute of Metrology Beijing, China*

**On-Chip Cancellation of Parasitic Effects for Dielectric Permittivity Measurement**  
C Song and P Wang  
*Clemson University, SC, USA*

**A Method for Automatic Tuner Verification**  
E M Johnson  
*Freescale Semiconductor, Tempe, AZ, USA*